Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-16	V
Gate-Source Voltage	V_{GSS}	±8	V
Continuous Drain Current	I_D	-5	A
Pulsed Drain Current	I_{DM}	-23	A
Avalanche Current	I_{AS}	21	A
Avalanche energy L=0.5mH	E_{AS}	308	mJ

Tj7.0172 0 0 7Power Dissipation for single operation 300.51373002W-.0012 Tc6.291ef32 Tw[21)-4( )891.8(A)]T01 8

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=-250 A V_{GS}=0V	-16	-18		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-16V V_{GS}=0V			-1.0	A
Gate-Body leakage current	I_{GSS}	V_{DS}=0V V_{GS}=±8V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=VGS I_D=-250 A	-0.5	-0.6	-1.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V I_D=-2.0A		27	32	mΩ
		V_{GS}=-2.5V I_D=-2.0A		37.3	42	
		V_{GS}=-1.8V I_D=-2.0A		51	60	
Diode Forward Voltage	V_{SD}	I_S=-1A V_{GS}=0V		0.75		V
Total Gate Charge	Q_g	V_{GS}=-4.5V V_{DS}=-10V I_D				

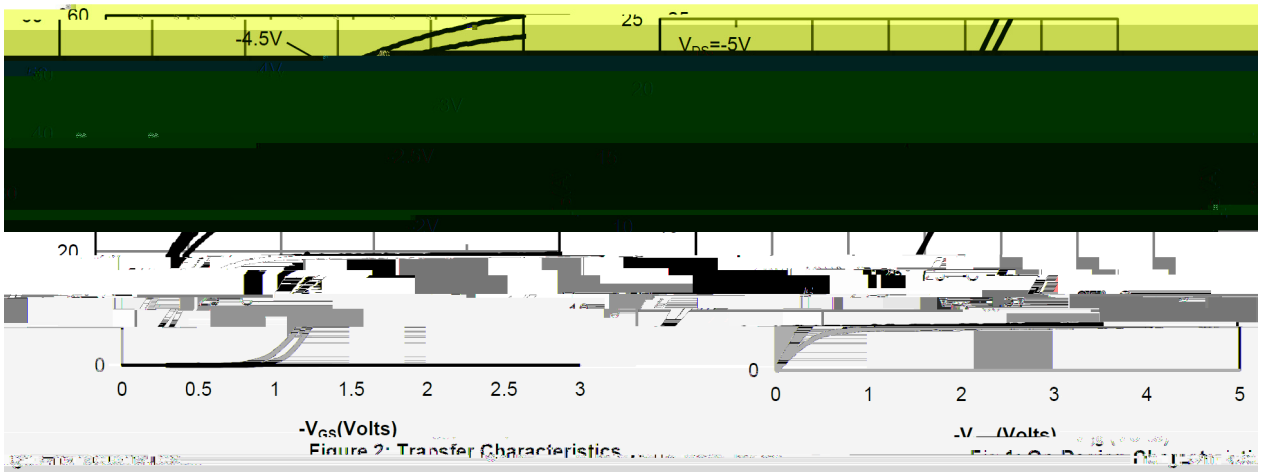
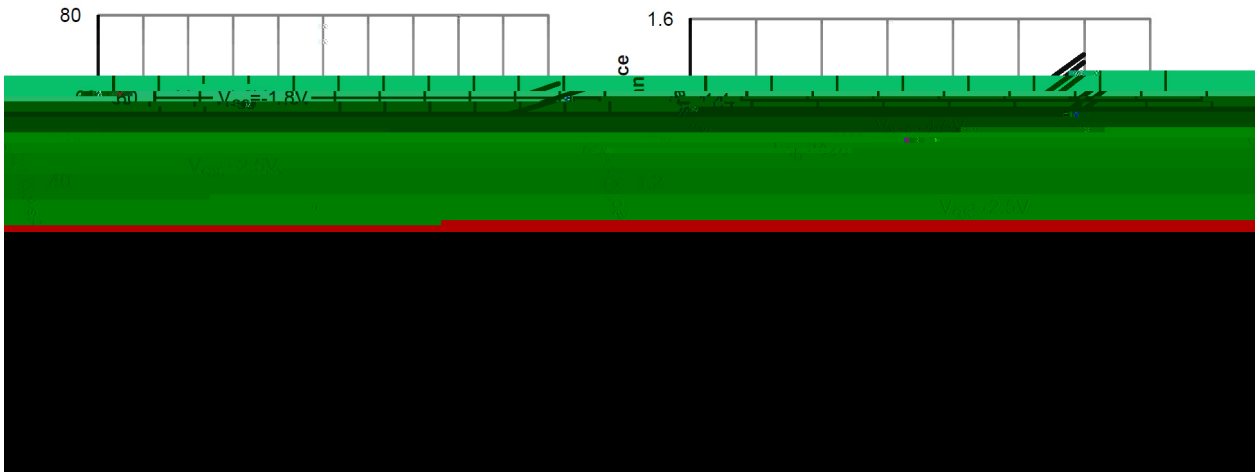


Figure 2: Transfer Characteristics



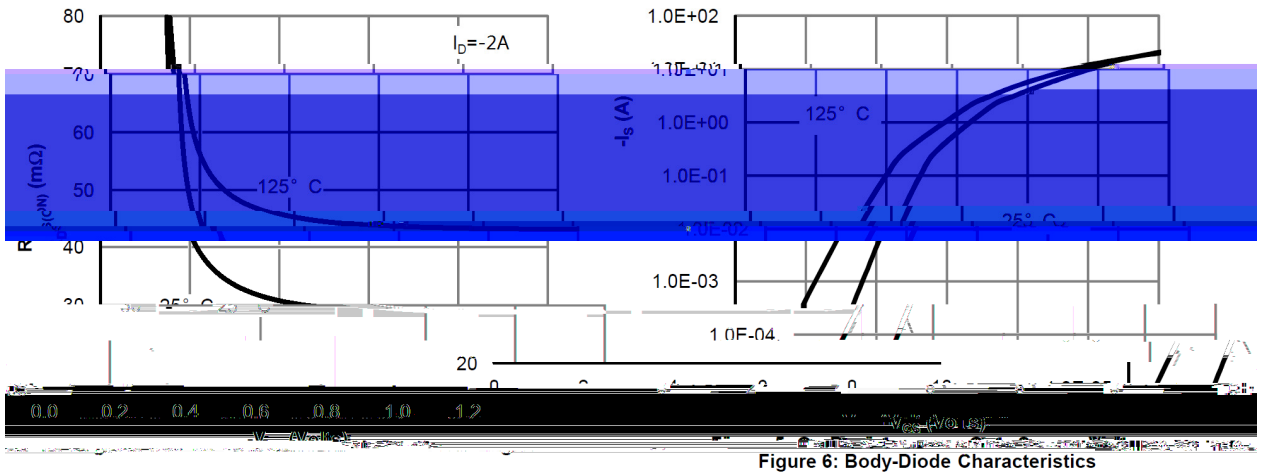


Figure 6: Body-Diode Characteristics

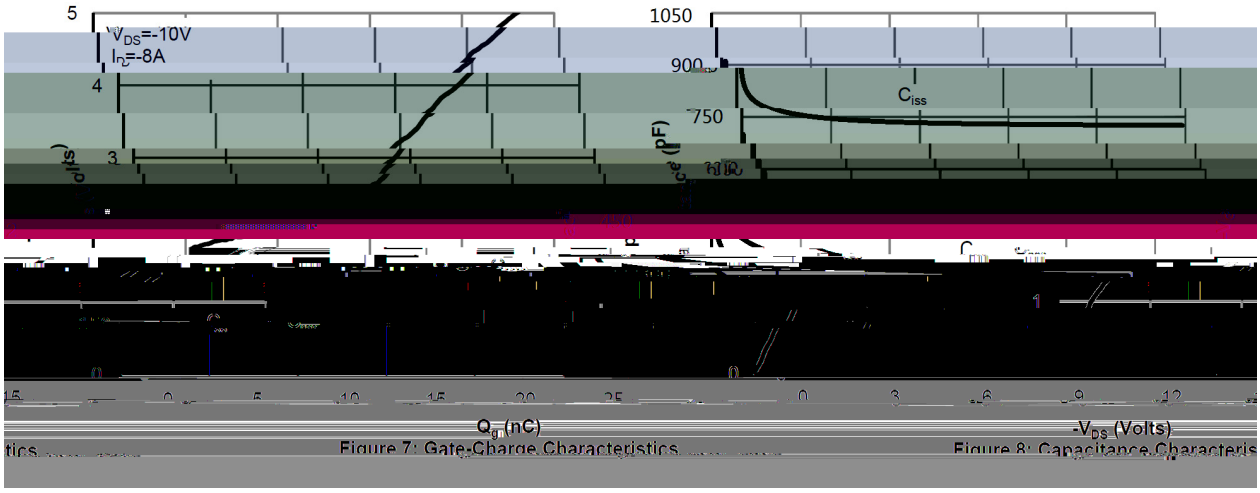
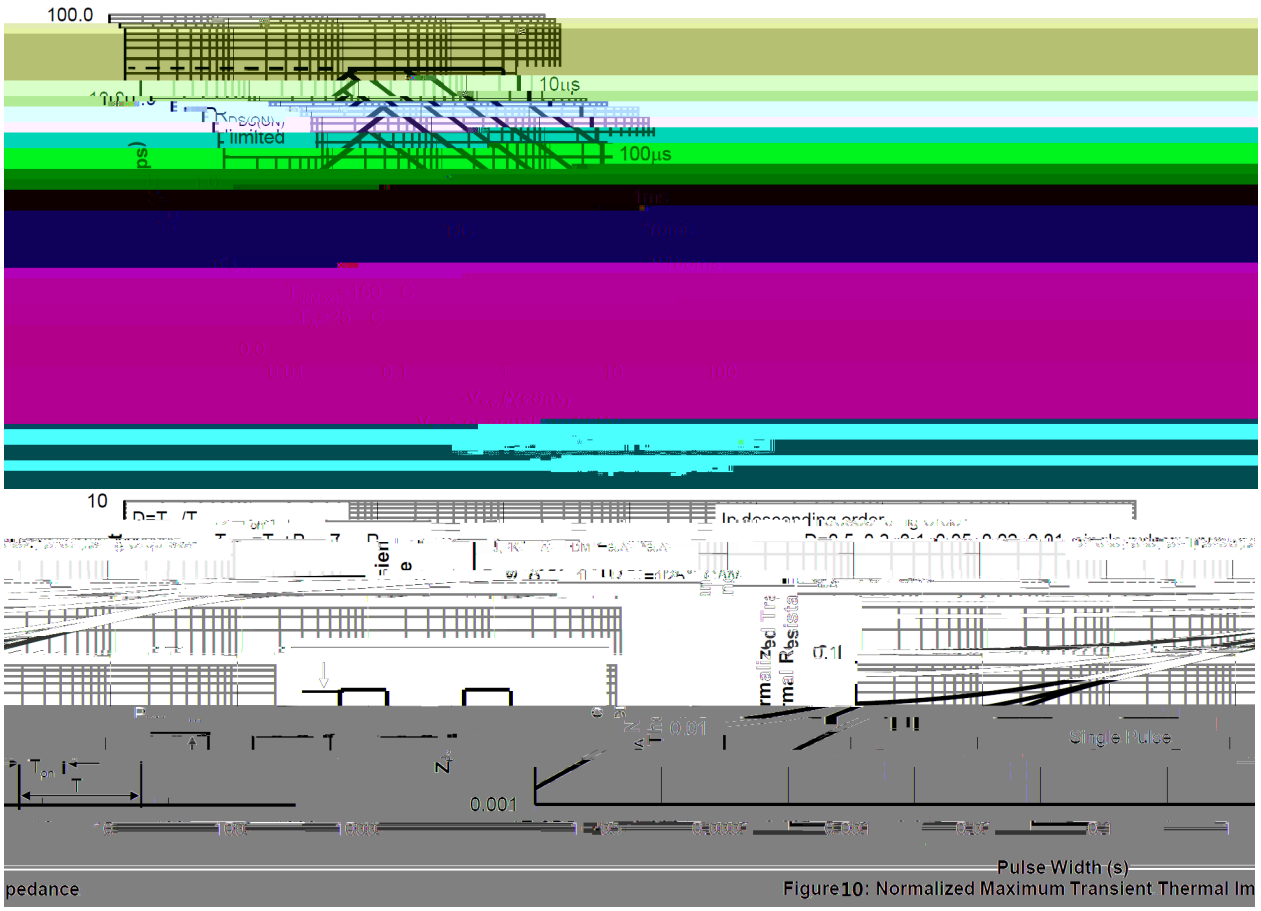


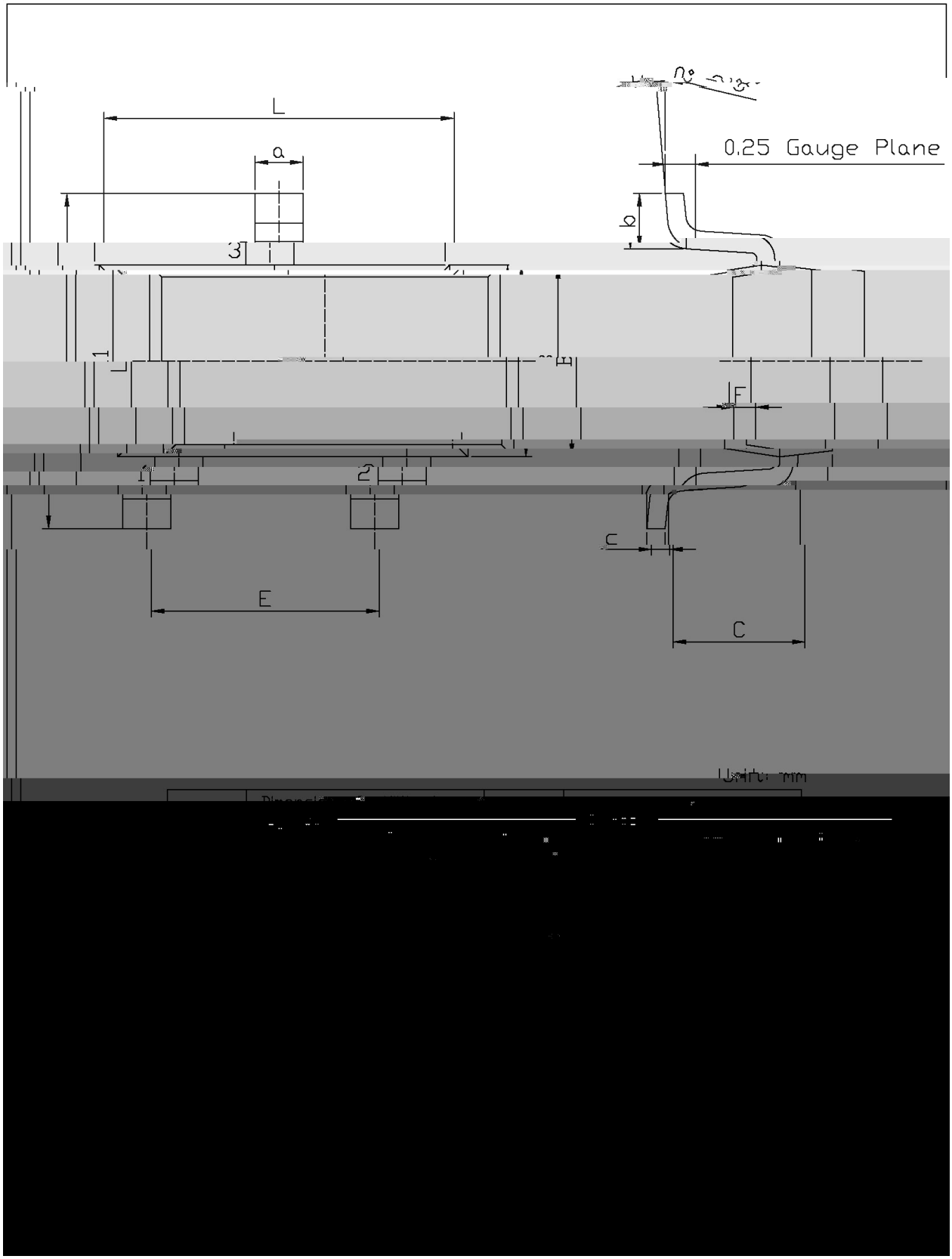
Figure 7: Gate-Charge Characteristics

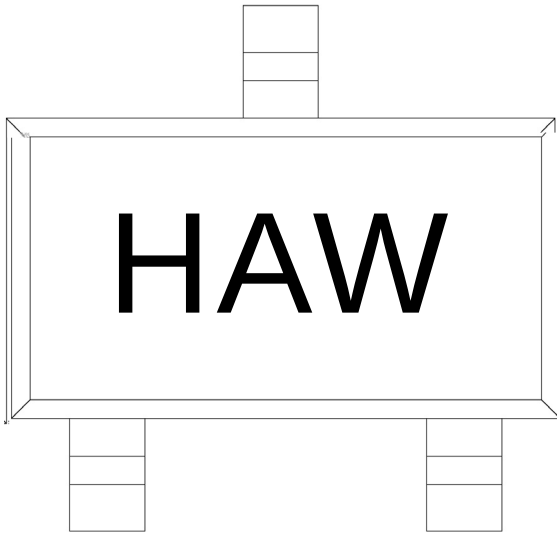
Figure 8: Capacitance Characteris



pedance

Figure10: Normalized Maximum Transient Thermal Im


L
a
3
1
2
E
0.25 Gauge Plane
b
F
c
C

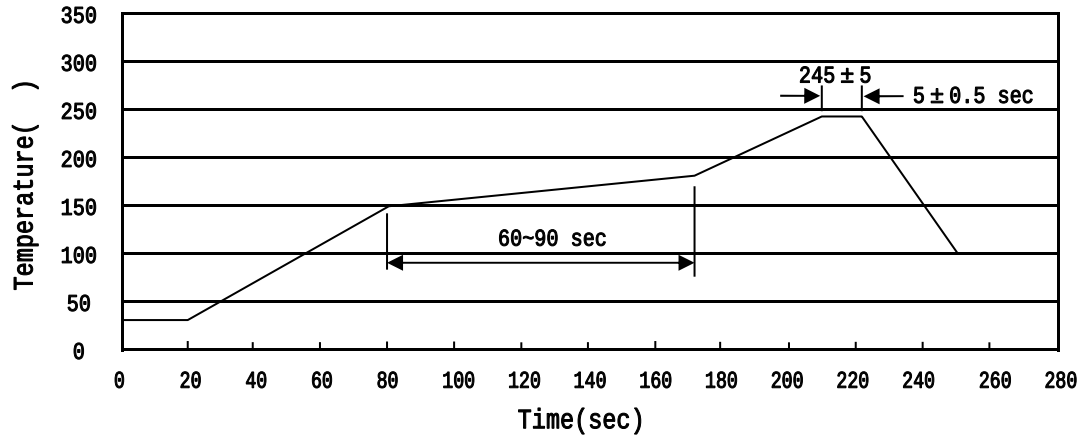


H:

AW:

Note:

H:	Company Code
AW	Product Type Code



Note:

1 150 180 60 90sec;

2 245±5 5±0.5sec;

3 2 10 /sec.

1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type	Units					Dimension		(unit mm³)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT23-3	3,000	10	30,000	4	120,000	7 ×8	210×205×205	445×435×230